



DMP1070UCA3

Product Summary

V _{DSS}	R _{DS(ON)} Max	Ι _D T _A = +25°C
-12V	70mΩ @ V _{GS} = -4.5V	-3.6A
	100mΩ @ V _{GS} = -2.5V	-3.0A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management
- Load Switch
- Battery Protection

P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

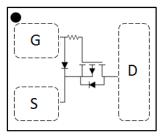
- Low Qg & Qgd
- Small Footprint
- Low Profile 0.22mm Height
- ESD Protected Gate 4kV HBM
 Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: X4-DSN0607-3
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu or NiAu. Solderable per MIL-STD-202, Method 208 @

X4-DSN0607-3





Top View Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Pitch	Packaging	Site		
DMP1070UCA3-7	X4-DSN0607-3	4mm	3000/Tape & Reel	A		
DMP1070UCA3-7A	X4-DSN0607-3	2mm	10000/Tape & Reel	В		
Notes: 1. No purposely adde	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Site A:		Site B:	
• M9 YM	$\begin{array}{l} M9 = \mbox{Product Type Marking Code} \\ YM = \mbox{Date Code Marking} \\ Y = \mbox{Year (ex: G = 2019)} \\ M = \mbox{Month (ex: 9 = September)} \end{array}$	• \ \ \ \ \ \ \ \ \ \ \	

Date Code Key

Year	2019	20	20	2021	2022	20	23	2024	2025	20	26	2027
Code	G	ŀ	4	I	J	ł	<	L	М	١	1	0
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-12	V	
Gate-Source Voltage		V _{GSS}	-6	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	T _A = +25°C T _A = +70°C	ID	-3.6 -2.9	А
Continuous Drain Current (Note 5) V_{GS} = -2.5V	T _A = +25°C T _A = +70°C	ID	-3.0 -2.4	А
Pulsed Drain Current (Note 6)	•	IDM	-15	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	PD	0.71	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 7)	R _{0JA}	179.3	°C/W
Power Dissipation (Note 5)	PD	1.36	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R _{0JA}	92.2	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	—	V	$V_{GS} = 0V, I_D = -250 \mu A$		
Zero Gate Voltage Drain Current TJ = +25°C	IDSS			-50	nA	$V_{DS} = -9.6V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	-25	nA	$V_{GS} = -5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	-0.40	-0.66	-0.95	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			52	70		$V_{GS} = -4.5V, I_D = -0.4A$		
Static Drain-Source On-Resistance			69	100	mΩ	$V_{GS} = -2.5V, I_D = -0.4A$		
	R _{DS(ON)}	_	93	150	11122	$V_{GS} = -1.8V, I_{D} = -0.4A$		
		_	120	210		V _{GS} = -1.5V, I _D = -0.1A		
Diode Forward Voltage	V _{SD}	_	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -0.4A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	Ciss		147					
Output Capacitance	Coss		79	_	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1MHz		
Reverse Transfer Capacitance	Crss		30					
Series Gate Resistance	R _G	_	13	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$		
Total Gate Charge	Qg	_	1.45					
Gate-Source Charge	Q _{gs}	_	0.14	_	nC	$V_{DS} = -6V, V_{GS} = -4.5V,$		
Gate-Drain Charge	Q _{qd}	_	0.28		nc	I _D = -0.4A		
Gate Charge at V _{TH}	Q _{g(th)}	_	0.10					
Turn-On Delay Time	t _{D(ON)}	_	3.2					
Turn-On Rise Time	t _R		6.0			$V_{DS} = -6V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	8.6		ns	$R_G = 0\Omega$, $I_D = -0.4A$		
Turn-Off Fall Time	t _F	_	5.8	_				

Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 Repetitive rating, pulse width limited by junction temperature.
 Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.

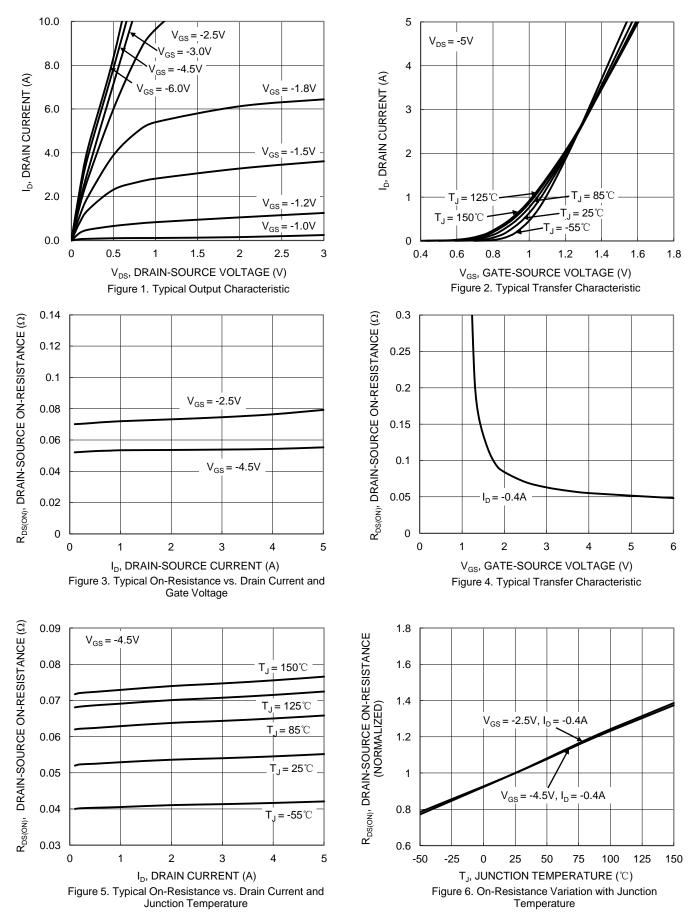
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to production testing.

Notes:

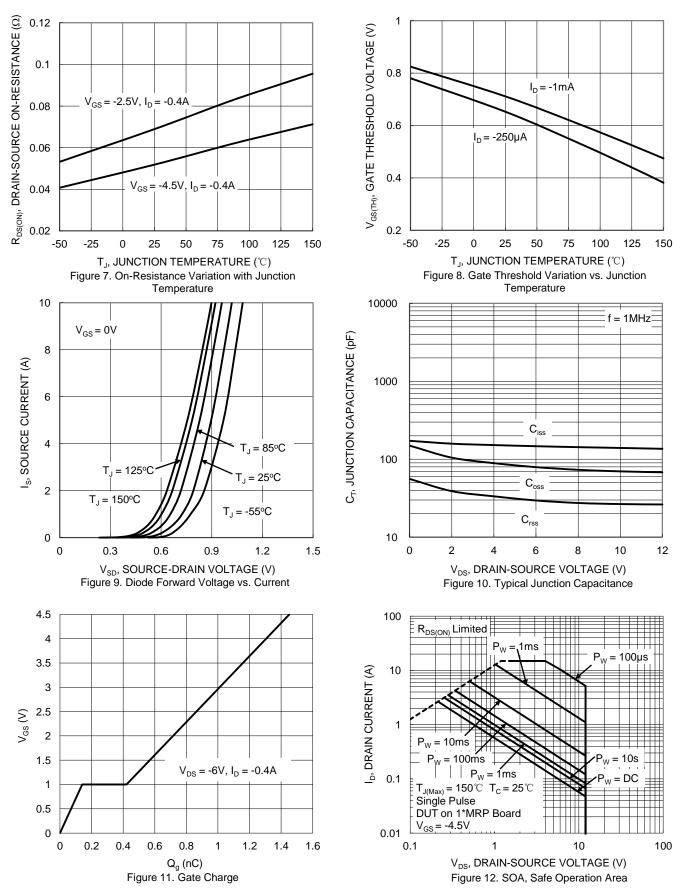


DMP1070UCA3

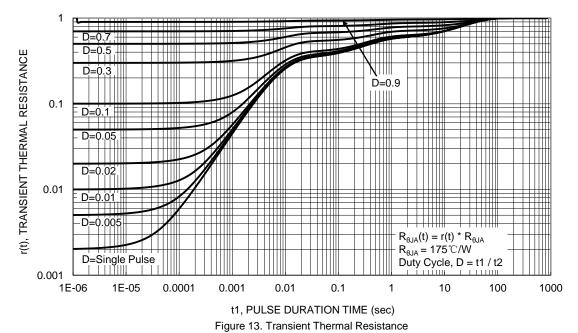




DMP1070UCA3





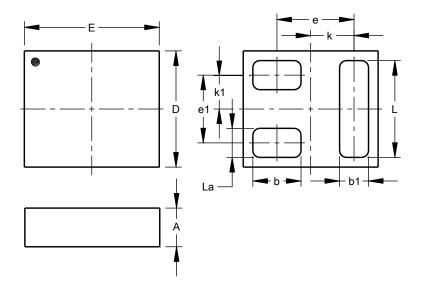




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN0607-3

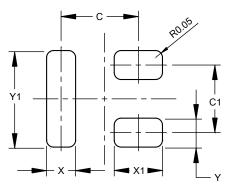


	X4-DSN0607-3						
Dim	Min	Max	Тур				
Α	0.18	0.22	0.20				
b	0.24	0.26	0.25				
b1	0.14	0.16	0.15				
D	0.56	0.64	0.60				
Е	0.65	0.73	0.69				
е			0.40				
e1			0.35				
k			0.225				
k1			0.175				
L	0.49	0.51	0.50				
La	0.14	0.16	0.15				
All	Dimen	sions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN0607-3



Dimensions	Value (in mm)
С	0.40
C1	0.35
Х	0.15
X1	0.25
Y	0.15
Y1	0.50



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Diodes Incorporated: DMP1070UCA3-7